

ACPL-H342 and ACPL-K342

2.5A Output Current IGBT Gate Drive Optocoupler with Active Miller Clamp, Rail-to-Rail Output Voltage, and UVLO in Stretched SO8

Description

The ACPL-H342 and ACPL-K342 contain an AlGaAs LED, which is optically coupled to an integrated circuit with a power output stage. This optocoupler is ideally suited for driving power IGBTs and MOSFETs used in motor control inverter applications. The high operating voltage range of the output stage provides the drive voltages required by gate controlled devices. The voltage and high peak output current supplied by this optocoupler make it ideally suited for direct driving IGBT with ratings up to 1200V/150A. For IGBTs with higher ratings, the ACPL-H342 and ACPL-K342 can be used to drive a discrete power stage which drives the IGBT gate. The ACPL-H342 and ACPL-K342 have the highest insulation voltage of $V_{IORM} = 891 V_{peak}$ and 1140 V_{peak} , respectively, in the IEC/EN/DIN EN 60747-5-5.

Features

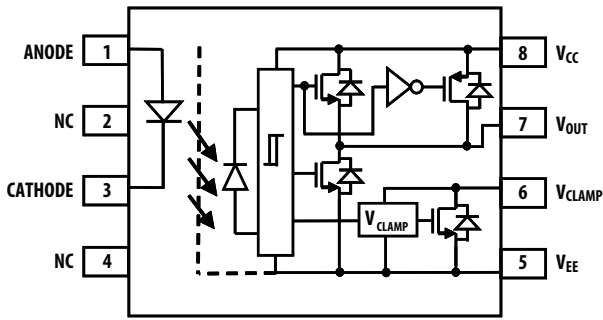
- 2.5A maximum peak output current
- 2.0A minimum peak output current
- Built-in active Miller clamp
- Rail-to-rail output voltage
- Fast propagation delay to minimize dead time
- $t_{PHL} < t_{PLH}$ to provide *anti-cross* conduction
- LED input threshold current hysteresis
- $I_{CC} = 2.5$ mA maximum supply current to allow boot-strap power supply
- Under voltage lock-out protection (UVLO) with hysteresis
- 40 kV/ μ s minimum common mode rejection (CMR) at $V_{CM} = 1500V$
- Wide operating V_{CC} range: 15V to 30V
- Industrial temperature range: $-40^{\circ}C$ to $105^{\circ}C$
- Safety approval:
 - UL Recognized 3750/5000 V_{RMS} for 1 minute
 - CSA
 - IEC/EN/DIN EN 60747-5-5 $V_{IORM} = 891/1140 V_{peak}$

Applications

- IGBT/MOSFET gate drive
- AC and brushless DC motor drives
- Renewable energy inverters
- Industrial inverters
- Switching power supplies

CAUTION! It is advised that normal static precautions be taken in handling and assembly of this component to prevent damage and/or degradation which can be induced by ESD. The components featured in this data sheet are not to be used in military or aerospace applications or environments.

Functional Diagram



NOTE: A 1- μ F bypass capacitor must be connected between pins V_{CC} and V_{EE} .

Table 1: Truth Table

LED	$V_{CC} - V_{EE}$ POSITIVE GOING (that is, TURN-ON)	$V_{CC} - V_{EE}$ NEGATIVE GOING (that is, TURN-OFF)	V_O	V_{CLAMP}
OFF	0V to 30V	0V to 30V	LOW	LOW
ON	0V to 11V	0V to 9.5V	LOW	LOW
ON	11V to 13.5V	9.5V to 12V	TRANSITION	TRANSITION
ON	13.5V to 30V	12V to 30V	HIGH	Hi-Z

Ordering Information

ACPL-H342 is UL Recognized with 3750 V_{RMS} for 1 minute per UL1577.

ACPL-K342 is UL Recognized with 5000 V_{RMS} for 1 minute per UL1577.

Table 2: Part Ordering Information

Part Number	Option (RoHS-Compliant)	Package	Surface Mount	Tape and Reel	UL 5000 V_{RMS} / 1 Minute Rating	IEC/EN/DIN EN 60747-5-5	Quantity
ACPL-H342	-000E	Stretched SO-8	X	—	—	—	80 per tube
	-500E		X	X	—	—	1000 per reel
	-060E		X	—	—	X	80 per tube
	-560E		X	X	—	X	1000 per reel
ACPL-K342	-000E	Stretched SO-8	X	—	X	—	80 per tube
	-500E		X	X	X	—	1000 per reel
	-060E		X	—	X	X	80 per tube
	-560E		X	X	X	X	1000 per reel

Example 1: ACPL-H342-560E to order product of Stretched SO-8 Surface Mount package in Tape and Reel packaging with IEC/EN/DIN EN 60747-5-5 Safety Approval and RoHS-compliant.

Example 2: ACPL-K342-000E to order product of Stretched SO-8 Surface Mount package in Tube packaging with UL 5000 V_{RMS} /1 minute and RoHS-compliant.

NOTE: Option data sheets are available. Contact your Broadcom sales representative or authorized distributor for information.

Package Outline Drawings

Figure 1: ACPL-H342 Outline Drawing

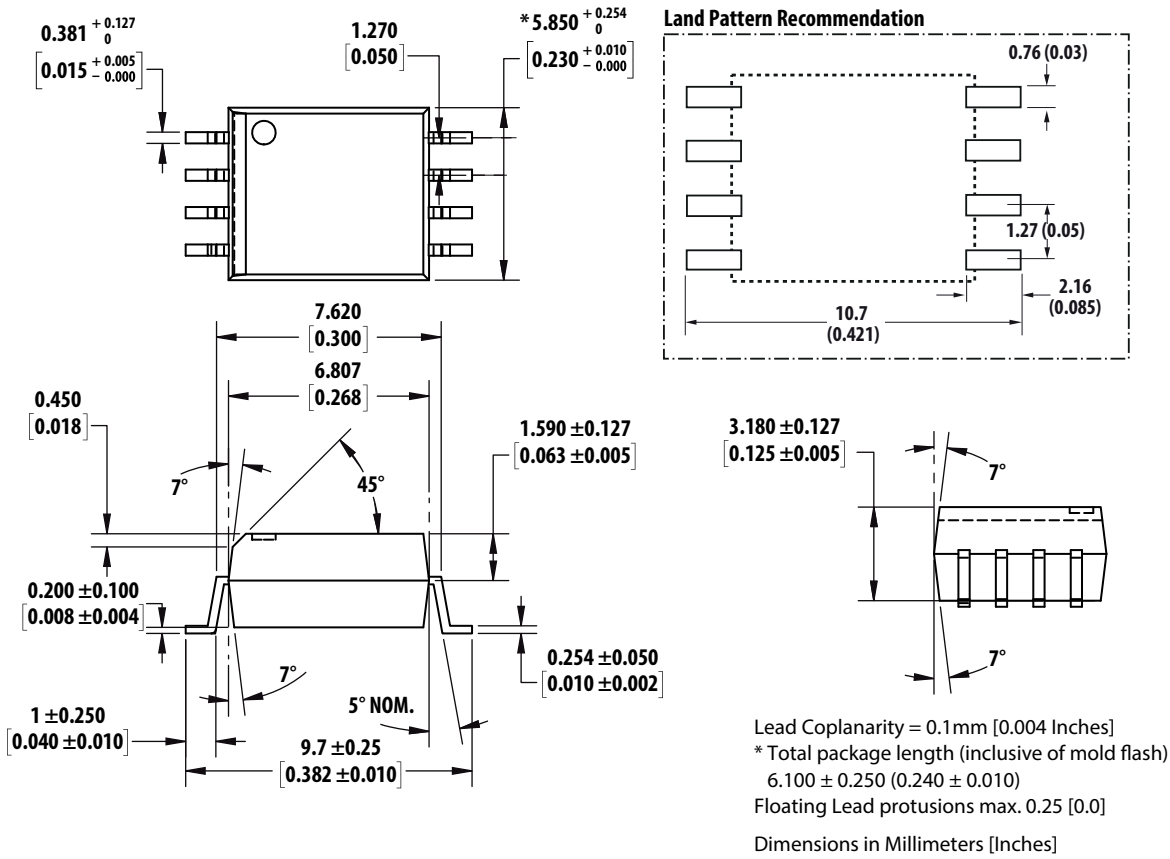
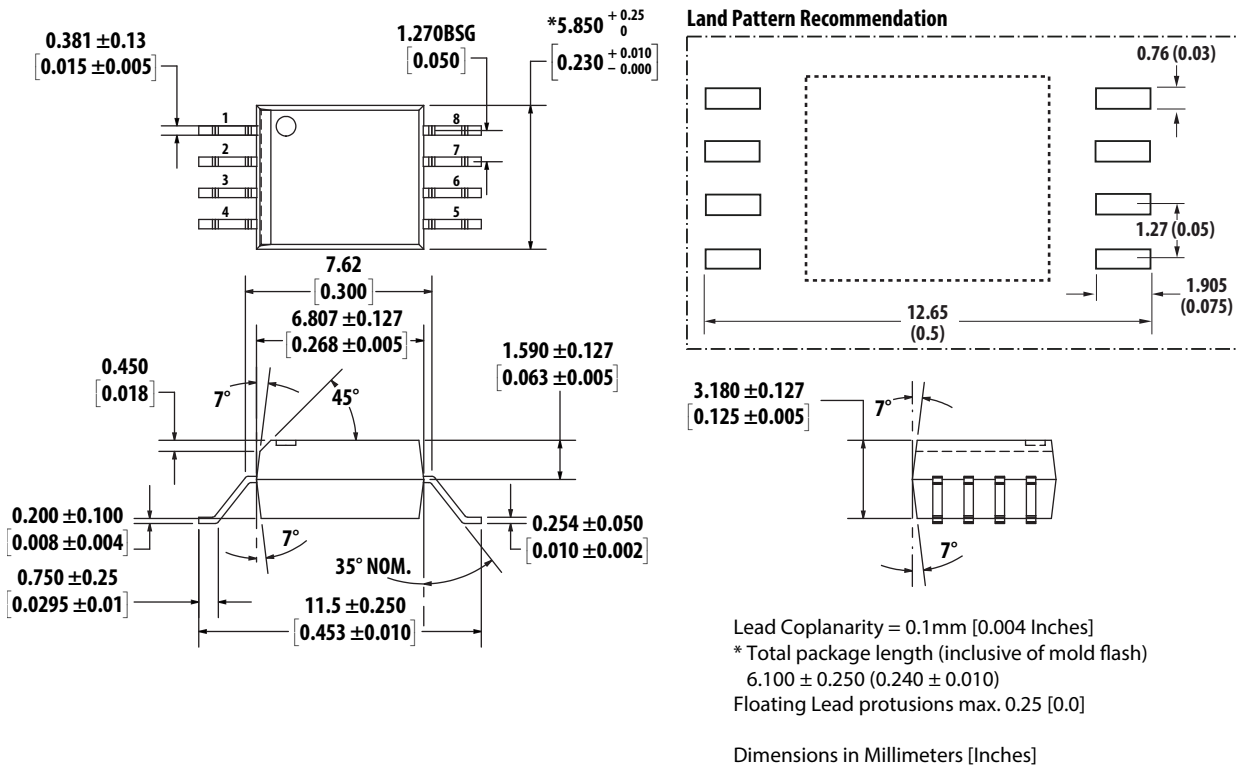


Figure 2: ACPL-K342 Outline Drawing



Recommended Pb-Free IR Profile

Recommended reflow condition as per JEDEC Standard, J-STD-020 (latest revision). Non-Halide Flux should be used.

Regulatory Information

The ACPL-H342 and ACPL-K342 are approved by the following organizations:

- UL
Recognized under UL 1577, component recognition program up to $V_{ISO} = 3750 V_{RMS}$ (ACPL-H342) and $V_{ISO} = 5000 V_{RMS}$ (ACPL-K342), File 55361.
- CSA
CSA Component Acceptance Notice 5, File CA 88324.
- IEC/EN/DIN EN 60747-5-5 (ACPL-H342/K342 Option 060 Only)
Maximum Working Insulation Voltage $V_{IORM} = 891V_{peak}$ (ACPL-H342) and $V_{IORM} = 1140 V_{peak}$ (ACPL-K342).

IEC/EN/DIN EN 60747-5-5 Insulation Characteristics (ACPL-H342/ACPL-K342 Option 060)

Table 3: IEC/EN/DIN EN 60747-5-5 Insulation Characteristics

Description	Symbol	ACPL-H342 Option 060	ACPL-K342 Option 060	Unit
Installation classification per DIN VDE 0110/39, Table 1f or rated mains voltage $\leq 150 V_{rms}$ for rated mains voltage $\leq 300 V_{rms}$ for rated mains voltage $\leq 450 V_{rms}$ for rated mains voltage $\leq 600 V_{rms}$ for rated mains voltage $\leq 1000 V_{rms}$	—	I – IV I – IV I – III I – III	I – IV I – IV I – IV I – III	—
Climatic Classification	—	40/105/21	40/105/21	—
Pollution Degree (DIN VDE 0110/39)	—	2	2	—
Maximum Working Insulation Voltage	V_{IORM}	891	1140	Vpeak
Input to Output Test Voltage, Method b ^a $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1s$, Partial discharge $< 5 pC$	V_{PR}	1671	2137	Vpeak
Input to Output Test Voltage, Method a ^a $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test, $t_m = 10s$, Partial discharge $< 5 pC$	V_{PR}	1426	1824	Vpeak
Highest Allowable Overvoltage ^a (Transient Overvoltage $t_{ini} = 60s$)	V_{IOTM}	6000	8000	Vpeak
Safety-limiting values – maximum values allowed in the event of a failure				
Case Temperature	T_S	175	175	°C
Input Current	$I_{S, INPUT}$	230	230	mA
Output Power	$P_{S, OUTPUT}$	600	600	mW
Insulation Resistance at T_S , $V_{IO} = 500V$	R_S	$>10^9$	$>10^9$	Ω

a. Refer to the IEC/EN/DIN EN 60747-5-5 Optoisolator Safety Standard section of the *Broadcom Regulatory Guide to Isolation Circuits*, AV02-2041EN, for a detailed description of Method a and Method b partial discharge test profiles.

NOTE: These optocouplers are suitable for *safe electrical isolation* only within the safety limit data. Maintenance of the safety data is ensured by means of protective circuits. Surface mount classification is Class A in accordance with CECC 00802.

Insulation and Safety Related Specifications

Table 4: Insulation and Safety Related Specifications

Parameter	Symbol	ACPL-H342	ACPL-K342	Unit	Conditions
Minimum External Air Gap (Clearance)	L (101)	7.0	8.0	mm	Measured from input terminals to output terminals, shortest distance through air.
Minimum External Tracking (Creepage)	L (102)	8.0	8.0	mm	Measured from input terminals to output terminals, shortest distance path along body.
Minimum Internal Plastic Gap (Internal Clearance)	—	0.08	0.08	mm	Through insulation distance conductor to conductor, usually the straight line distance thickness between the emitter and detector.
Tracking Resistance (Comparative Tracking Index)	CTI	>175	>175	V	DIN IEC 112/VDE 0303 Part 1.
Isolation Group	—	IIIa	IIIa	—	Material Group (DIN VDE 0110, 1/89, Table 1).

NOTE: All Broadcom data sheets report the creepage and clearance inherent to the optocoupler component itself. These dimensions are needed as a starting point for the equipment designer when determining the circuit insulation requirements. However, once mounted on a printed circuit board, minimum creepage and clearance requirements must be met as specified for individual equipment standards. For creepage, the shortest distance path along the surface of a printed circuit board between the solder fillets of the input and output leads must be considered (the recommended land pattern does not necessarily meet the minimum creepage of the device). There are recommended techniques such as grooves and ribs which can be used on a printed circuit board to achieve desired creepage and clearances. The creepage and clearance distances also change depending on factors, such as pollution degree and insulation level.

Absolute Maximum Ratings

Table 5: Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Unit	Note
Storage Temperature	T_S	-55	125	°C	—
Operating Temperature	T_A	-40	105	°C	—
Output IC Junction Temperature	T_J	—	125	°C	—
Average Input Current	$I_{F(AVG)}$	—	25	mA	a
Peak Transient Input Current (<1 ms pulse width, 300 pps)	$I_{F(TRAN)}$	—	1	A	—
Reverse Input Voltage	V_R	—	5	V	—
“High” Peak Output Current	$I_{OH(PEAK)}$	—	2.5	A	b
“Low” Peak Output Current	$I_{OL(PEAK)}$	—	2.5	A	b
Peak Clamp Sink Current	I_{CLAMP}	—	2.5	A	b
Total Output Supply Voltage	$(V_{CC} - V_{EE})$	0	35	V	—
Output Voltage	$V_{O(PEAK)}$	-0.5	V_{CC}	V	—
Output IC Power Dissipation	P_O	—	500	mW	c
Total Power Dissipation	P_T	—	550	mW	d
Lead Solder Temperature	260°C for 10s, 1.6 mm below seating plane				

a. Derate linearly above 70°C free-air temperature at a rate of 0.3 mA/°C.

b. Maximum pulse width = 10 μ s.

c. Derate linearly above 85°C free-air temperature at a rate of 12.5 mW/°C.

d. Derate linearly above 85°C free-air temperature at a rate of 13.75 mW/°C. The maximum LED junction temperature should not exceed 125°C.

Recommended Operating Conditions

Table 6: Recommended Operating Conditions

Parameter	Symbol	Min.	Max.	Unit	Note
Operating Temperature	T_A	-40	105	°C	—
Output Supply Voltage	$(V_{CC} - V_{EE})$	15	30	V	—
Input Current (ON)	$I_{F(ON)}$	7	16	mA	—
Input Voltage (OFF)	$V_{F(OFF)}$	-3.6	0.8	V	—

Electrical Specifications (DC)

Unless otherwise noted, all typical values are at $T_A = 25^\circ\text{C}$, $V_{CC} - V_{EE} = 30\text{V}$, $V_{EE} = \text{Ground}$; all Minimum/Maximum specifications are at recommended operating conditions ($T_A = -40^\circ\text{C}$ to 105°C , $I_{F(\text{ON})} = 7\text{ mA}$ to 16 mA , $V_{F(\text{OFF})} = -3.6\text{V}$ to 0.8V , $V_{CC} = 15\text{V}$ to 30V , $V_{EE} = \text{Ground}$).

Table 7: Electrical Specifications (DC)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Figure	Note
High Level Peak Output Current	I_{OH}	-0.5	-1.2	—	A	$V_O = V_{CC} - 4\text{V}$	Figure 5, Figure 6, Figure 25	a
		-2.0	—	—	A	$V_O = V_{CC} - 15\text{V}$		b
Low Level Peak Output Current	I_{OL}	0.5	2.7	—	A	$V_O = V_{EE} + 2.5\text{V}$	Figure 8, Figure 9, Figure 26	a
		2.0	—	—	A	$V_O = V_{EE} + 15\text{V}$		b
High Output Transistor RDS(ON)	$R_{\text{DS,OH}}$	—	2.6	5.0	Ω	$I_{\text{OH}} = -2.0\text{A}$	Figure 10	—
Low Output Transistor RDS(ON)	$R_{\text{DS,OL}}$	—	0.8	2.0	Ω	$I_{\text{OL}} = 2.0\text{A}$	Figure 11	—
Clamp Output Peak Current	I_{CLAMP}	1.0	2.5	—	A	$V_O = V_{EE} + 2.5\text{V}$	Figure 16, Figure 18, Figure 29	b
Clamp Pin Threshold	V_{ICLAMP}	—	2.3	—	V	—	Figure 17,Fi gure 18, Figure 30	—
Clamp Output Transistor RDS(ON)	$R_{\text{DS,CLAMP}}$	—	0.8	2.0	Ω	$I_{\text{CLAMP}} = 1.5\text{A}$	—	—
High Level Output Voltage	V_{OH}	$V_{CC} - 2.0$	—	—	V	$I_O = -100\text{ mA}$	Figure 4, Figure 6, Figure 27	c, d
High Level Output Voltage	V_{OH}	—	V_{CC}	—	V	$I_O = 0\text{ mA}$, $I_F = 10\text{ mA}$	Figure 3	—
Low Level Output Voltage	V_{OL}	—	0.07	0.25	V	$I_O = 100\text{ mA}$	Figure 7, Figure 9, Figure 28	—
High Level Supply Current	I_{CCH}	—	1.68	2.5	mA	$R_g = 10\Omega$, $C_g = 25\text{ nF}$, $I_F = 10\text{ mA}$,	Figure 12, Figure 13	—
Low Level Supply Current	I_{CCL}	—	2.0	2.5	mA	$R_g = 10\Omega$, $C_g = 25\text{ nF}$, $I_F = 0\text{ mA}$		—
Threshold Input Current Low to High	I_{FLH}	0.5	1.5	4.0	mA	$R_g = 10\Omega$, $C_g = 25\text{ nF}$, $V_O > 5\text{V}$	Figure 14, Figure 15, Figure 31	—
Threshold Input Voltage High to Low	V_{FHL}	0.8	—	—	V	—		—
Input Forward Voltage	V_F	1.2	1.55	1.95	V	$I_F = 10\text{ mA}$	Figure 24	—
Temperature Coefficient of Input Forward Voltage	$\Delta V_F / \Delta T_A$	—	-1.7	—	mV/ $^\circ\text{C}$	—		—
Input Reverse Breakdown Voltage	BV_R	5	—	—	V	$I_R = 100\text{ }\mu\text{A}$	—	—
Input Capacitance	C_{IN}	—	70	—	pF	$f = 1\text{ MHz}$, $V_F = 0\text{V}$	—	—

Table 7: Electrical Specifications (DC) (Continued)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Figure	Note
UVLO Threshold	V_{UVLO+}	11.0	12.3	13.5	V	$V_O > 5V, I_F = 10 \text{ mA}$	Figure 32	—
	V_{UVLO-}	9.5	10.7	12.0				—
UVLO Hysteresis	$UVLO_{HYS}$	—	1.4	—				—

- Maximum pulse width = 50 μs .
- Maximum pulse width = 10 μs .
- In this test, V_{OH} is measured with a DC load current. When driving capacitive loads, V_{OH} will approach V_{CC} as I_{OH} approaches 0 amps.
- Maximum pulse width = 1 ms.

Switching Specifications (AC)

Unless otherwise noted, all typical values are at $T_A = 25^\circ\text{C}$, $V_{CC} - V_{EE} = 30V$, $V_{EE} = \text{Ground}$; all Minimum/Maximum specifications are at recommended operating conditions ($T_A = -40^\circ\text{C}$ to 105°C , $I_{F(ON)} = 7 \text{ mA}$ to 16 mA , $V_{F(OFF)} = -3.6V$ to $0.8V$, $V_{CC} = 15V$ to $30V$, $V_{EE} = \text{Ground}$).

Table 8: Switching Specifications (AC)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Figure	Note
Propagation Delay Time to High Output Level	t_{PLH}	0.100	0.260	0.350	μs	$R_g = 10 \Omega, C_g = 25 \text{ nF}$, $f = 20 \text{ kHz}$, Duty Cycle = 50%, $I_F = 7 \text{ mA}$ to 16 mA , $V_{CC} = 15V$ to $30V$	Figure 19, Figure 20, Figure 21, Figure 22, Figure 23, Figure 33	a
Propagation Delay Time to Low Output Level	t_{PHL}	0.050	0.145	0.250	μs			
Propagation Delay Difference Between Any Two Parts	PDD ($t_{PHL} - t_{PLH}$)	-0.010	-0.100	-0.200	μs			
Rise Time	t_R	—	22	—	ns	$V_{CC} = 30V$	Figure 33	—
Fall Time	t_F	—	18	—	ns		—	—
Output High Level Common Mode Transient Immunity	$ CM_H $	40	50	—	kV/ μs	$T_A = 25^\circ\text{C}$, $I_F = 10 \text{ mA}$, $V_{CC} = 30V$, $V_{CM} = 1500V$ with split resistors	Figure 34	c, d
		25	35	—		$T_A = 25^\circ\text{C}$, $I_F = 10 \text{ mA}$, $V_{CC} = 30V$, $V_{CM} = 1000V$ without split resistors	—	—
Output Low Level Common Mode Transient Immunity	$ CM_L $	40	50	—	kV/ μs	$T_A = 25^\circ\text{C}$, $V_F = 0V$, $V_{CC} = 30V$, $V_{CM} = 1500V$ with split resistors	Figure 34	c, e
		25	35	—		$T_A = 25^\circ\text{C}$, $V_F = 0V$, $V_{CC} = 30V$, $V_{CM} = 1000V$ without split resistors	—	—

- This load condition approximates the gate load of a 1200V/150A IGBT.
- The difference between t_{PHL} and t_{PLH} between any two ACPL-H342 parts under the same test condition.
- Pins 2 and 4 need to be connected to LED common.
- Common mode transient immunity in the high state is the maximum tolerable dV_{CM}/dt of the common mode pulse, V_{CM} , to assure that the output will remain in the high state (that is, $V_O > 15.0V$).
- Common mode transient immunity in a low state is the maximum tolerable dV_{CM}/dt of the common mode pulse, V_{CM} , to assure that the output will remain in a low state (that is, $V_O < 1.0V$).

Package Characteristics

Unless otherwise noted, all typical values are at $T_A = 25^\circ\text{C}$; all Minimum/Maximum specifications are at recommended operating conditions.

Table 9: Package Characteristics

Parameter	Symbol	Device	Min.	Typ.	Max.	Unit	Test Conditions	Figure	Note
Input-Output Momentary Withstand Voltage ^a	V_{ISO}	ACPL-H342	3750	—	—	V_{RMS}	$R_H < 50\%$, $t = 1 \text{ min.}$, $T_A = 25^\circ\text{C}$	—	b, c
		ACPL-K342	5000	—	—	V_{RMS}	$R_H < 50\%$, $t = 1 \text{ min.}$, $T_A = 25^\circ\text{C}$	—	c, d
Input-Output Resistance	R_{I-O}	—	—	$> 50^{12}$	—	Ω	$V_{I-O} = 500 \text{ VDC}$	—	c
Input-Output Capacitance	C_{I-O}	—	—	0.2	—	pF	$f = 1 \text{ MHz}$	—	—
LED-to-Ambient Thermal Resistance	R_{11}	—	—	145	—	$^\circ\text{C/W}$	Thermal Model in Application Notes Below	—	e
LED-to-Detector Thermal Resistance	R_{12}, R_{21}	—	—	25, 38	—				
Detector-to-Ambient Thermal Resistance	R_{22}	—	—	46	—				

- The input-output momentary withstand voltage is a dielectric voltage rating that should not be interpreted as an input-output continuous voltage rating. For the continuous voltage rating, refer to your equipment level safety specification or Broadcom Application Note 1074, *Optocoupler Input-Output Endurance Voltage*.
- In accordance with UL1577, each optocoupler is proof tested by applying an insulation test voltage $\geq 4500 \text{ Vrms}$ for 1 second (leakage detection current limit, $I_{I-O} \leq 5 \text{ mA}$).
- Device considered a two-terminal device: pins 1, 2, 3, and 4 shorted together and pins 5, 6, 7, and 8 shorted together.
- In accordance with UL1577, each optocoupler is proof tested by applying an insulation test voltage $\geq 6000 \text{ Vrms}$ for 1 second (leakage detection current limit, $I_{I-O} \leq 5 \text{ mA}$).
- The device was mounted on a high conductivity test board as per JEDEC 51-7.

Figure 3: High Output Rail Voltage versus Temperature

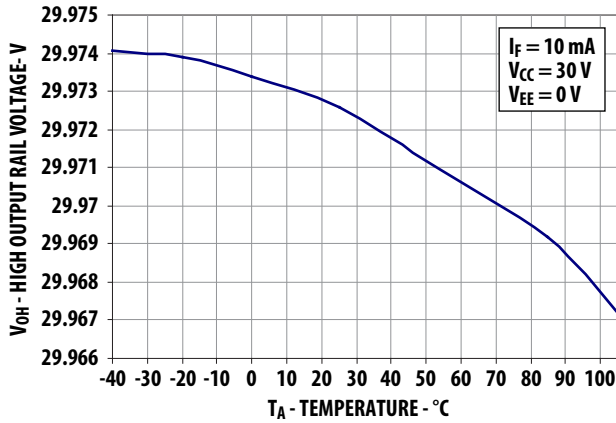


Figure 6: I_{OH} versus V_{OH}

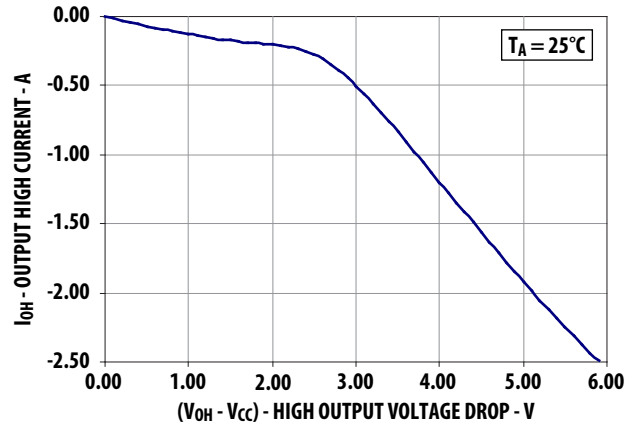


Figure 4: V_{OH} versus Temperature

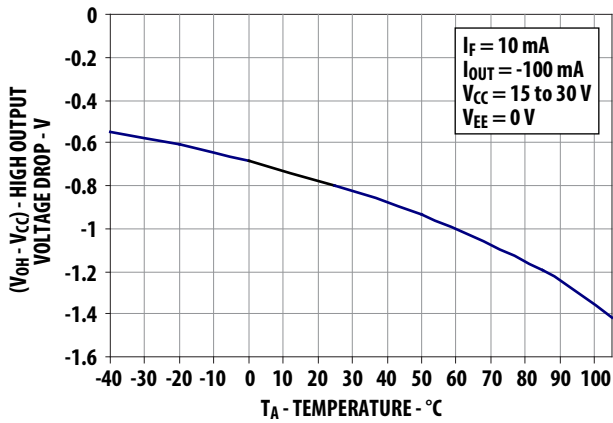


Figure 7: V_{OL} versus Temperature

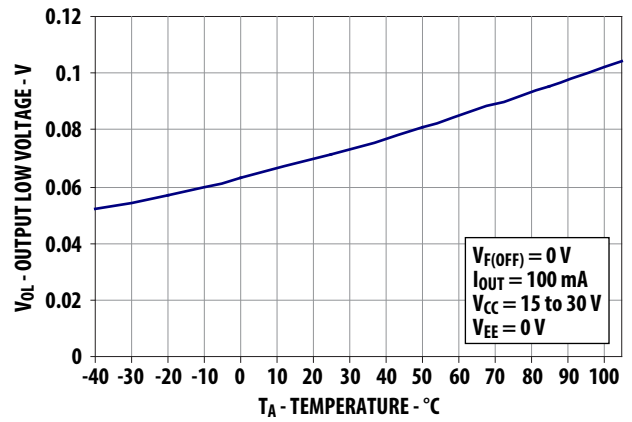


Figure 5: I_{OH} versus Temperature

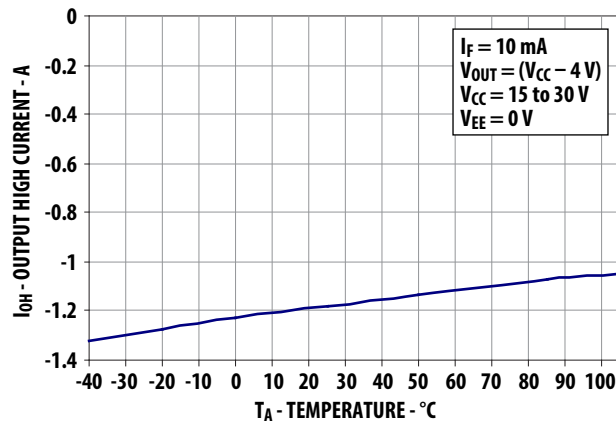


Figure 8: I_{OL} versus Temperature

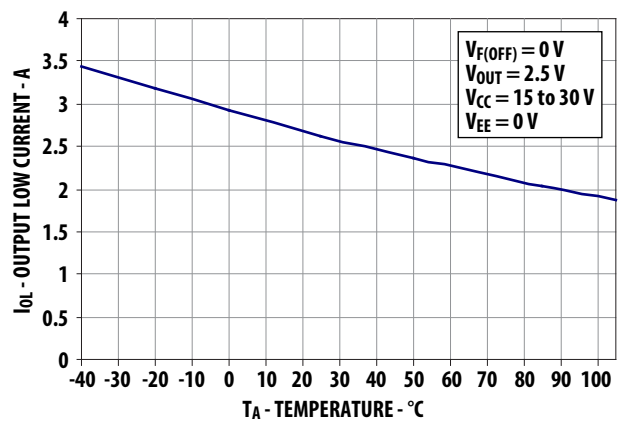


Figure 9: I_{OL} versus V_{OL}

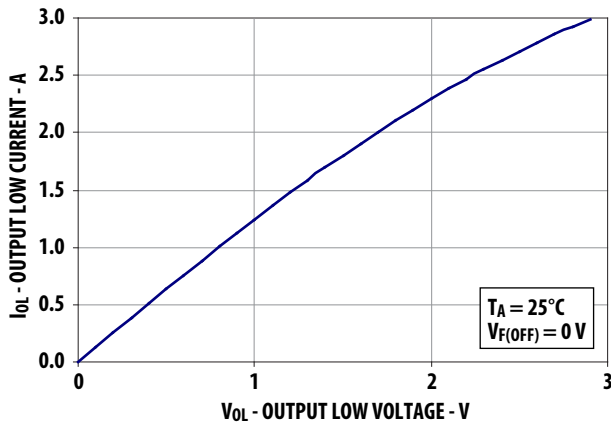


Figure 12: I_{CC} versus Temperature

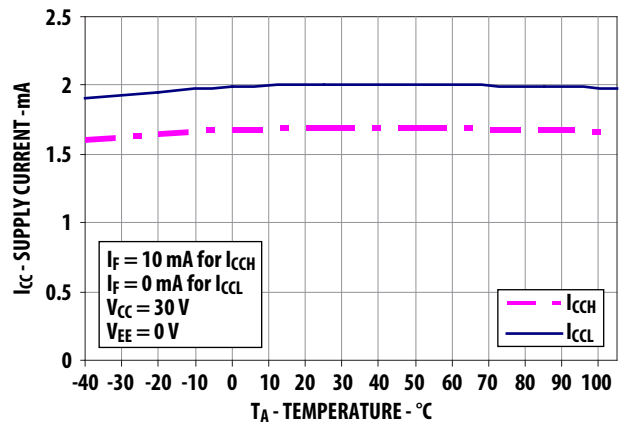


Figure 10: $R_{DS,OH}$ versus Temperature

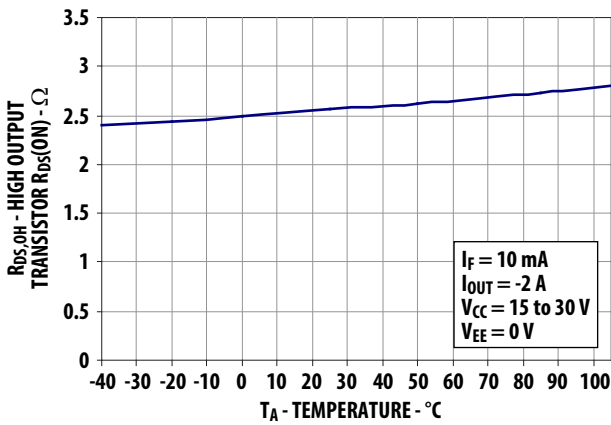


Figure 13: I_{CC} versus V_{CC}

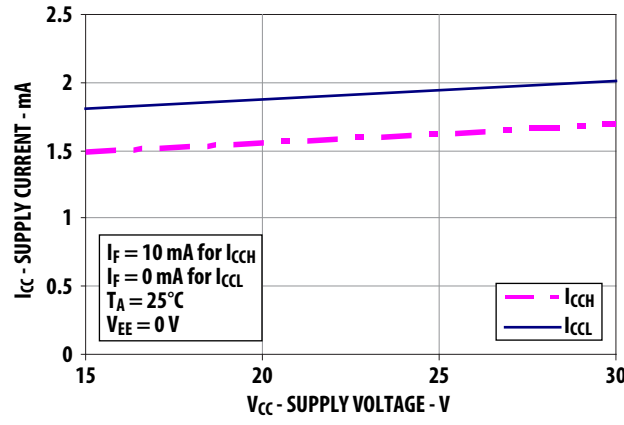


Figure 11: $R_{DS,PL}$ versus Temperature

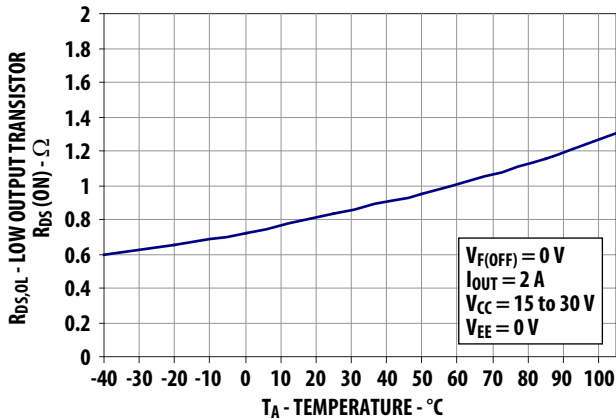


Figure 14: I_{FLH} Hysteresis

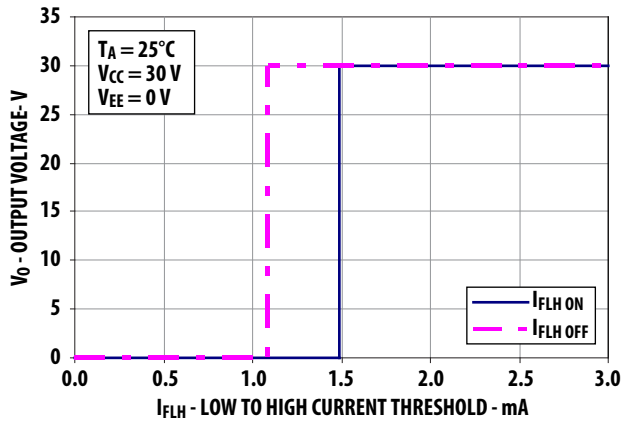


Figure 15: I_{FLH} versus Temperature

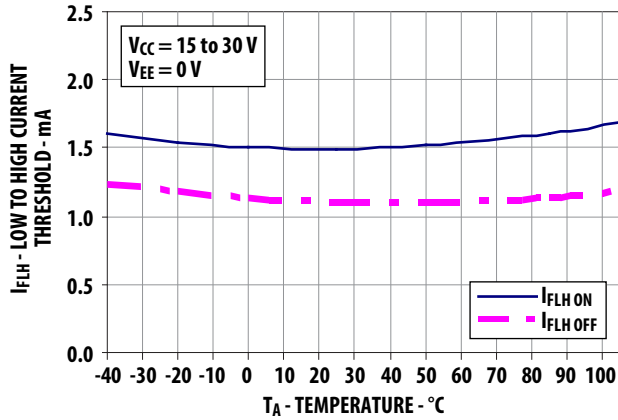


Figure 18: I_{CLAMP} versus V_{tCLAMP}

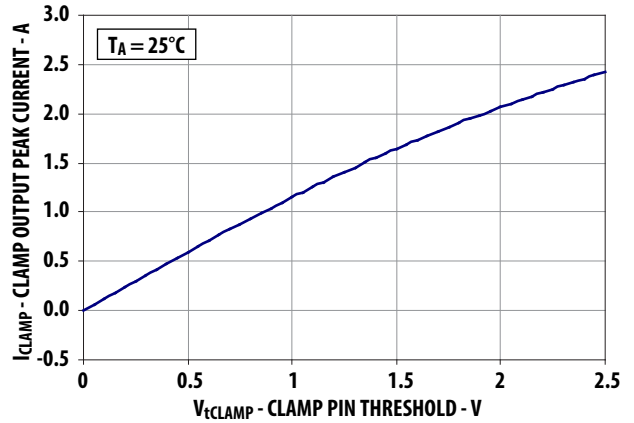


Figure 16: I_{CLAMP} versus Temperature

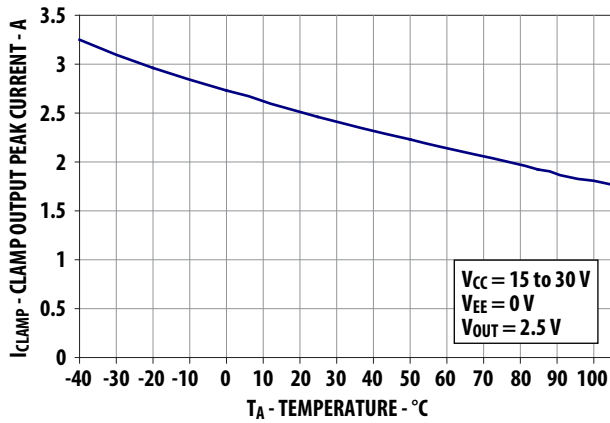


Figure 19: Propagation Delay versus V_{CC}

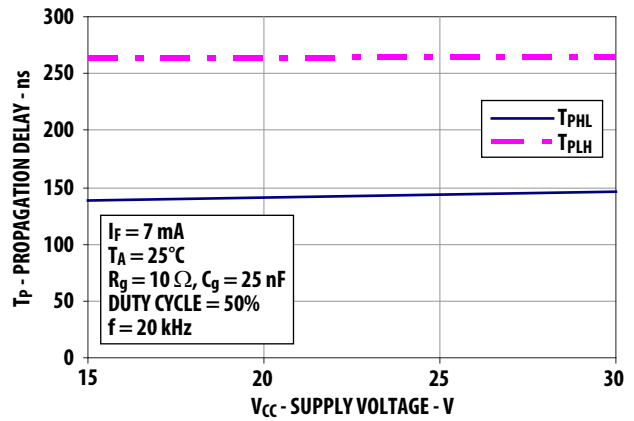


Figure 17: V_{tCLAMP} versus Temperature

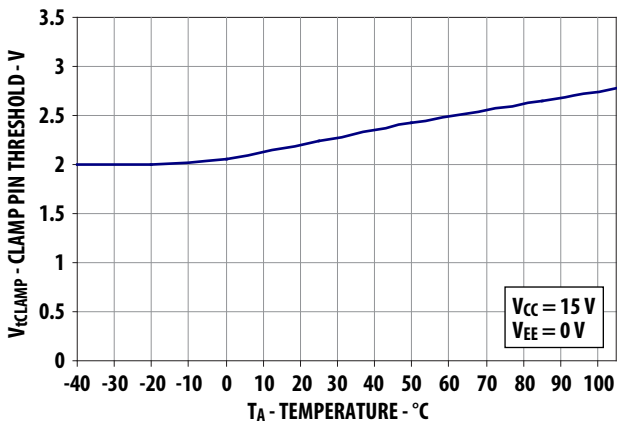


Figure 20: Propagation Delay versus I_F

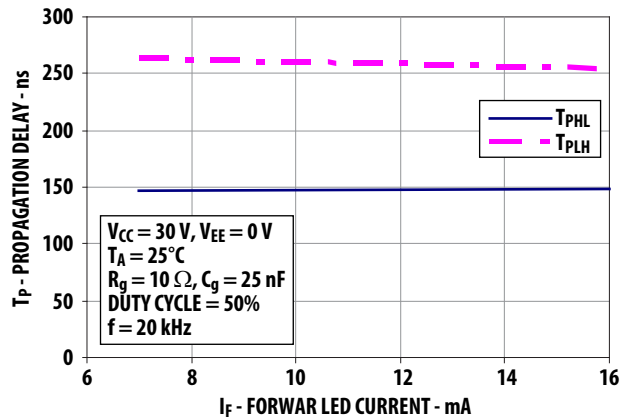


Figure 21: Propagation Delay versus Temperature

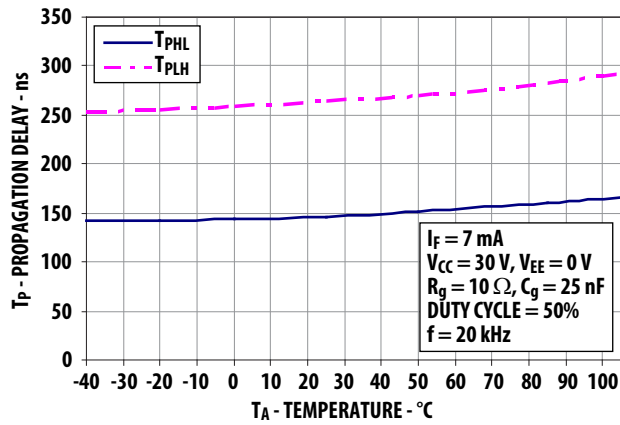


Figure 23: Propagation Delay versus Cg

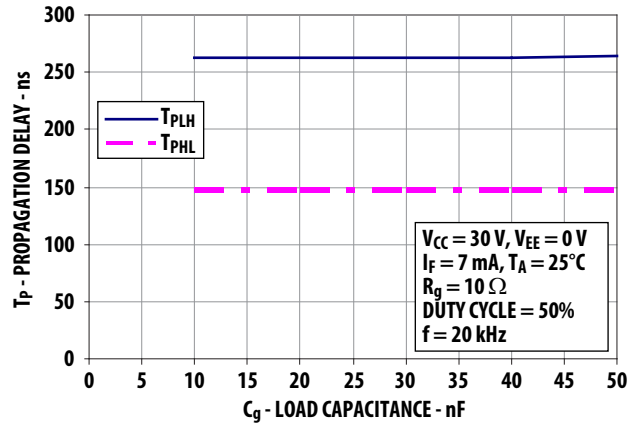


Figure 22: Propagation Delay versus Rg

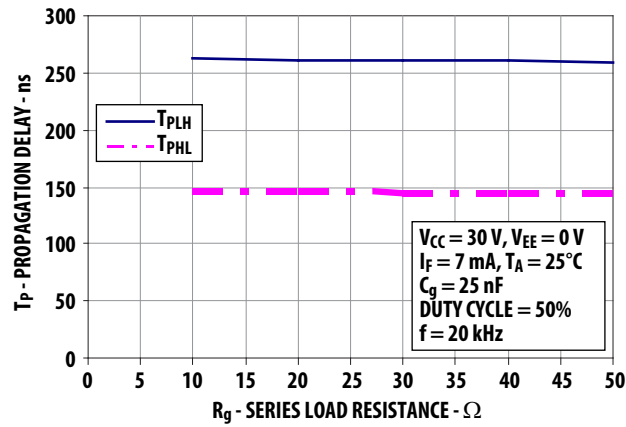


Figure 24: Input Current versus Forward Voltage

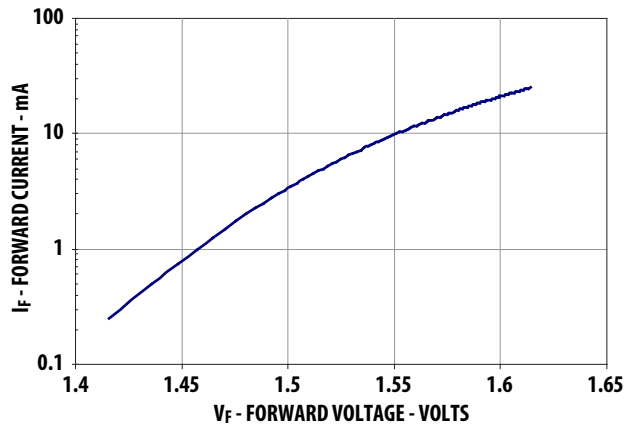


Figure 25: I_{OH} Test Circuit

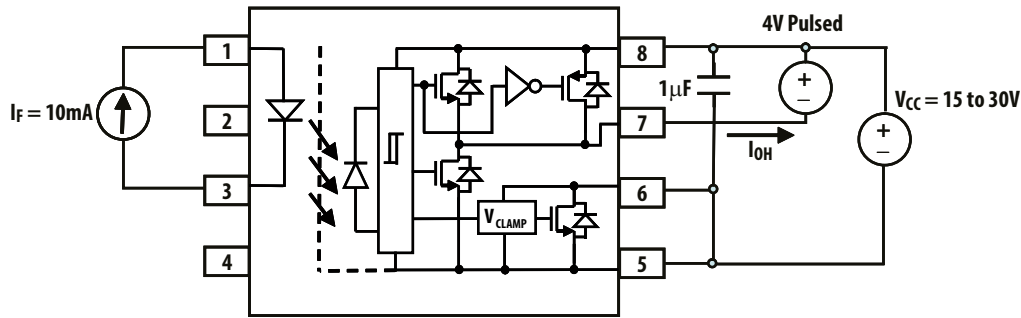


Figure 26: I_{OL} Test Circuit

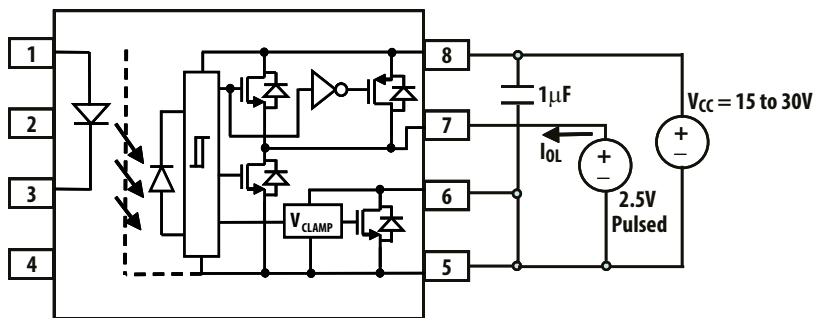


Figure 27: V_{OH} Test Circuit

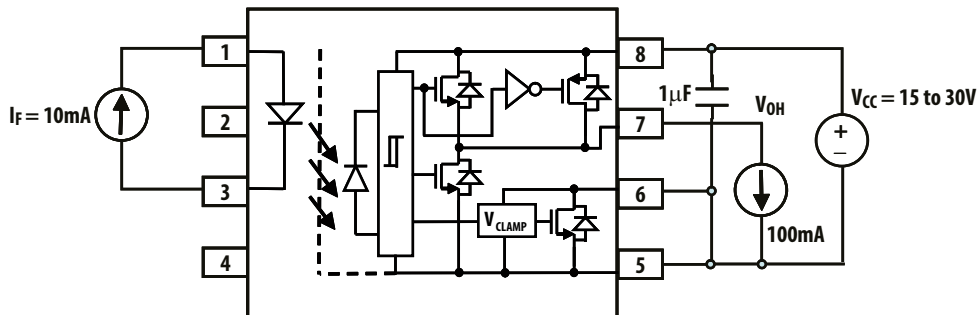


Figure 28: V_{OL} Test Circuit

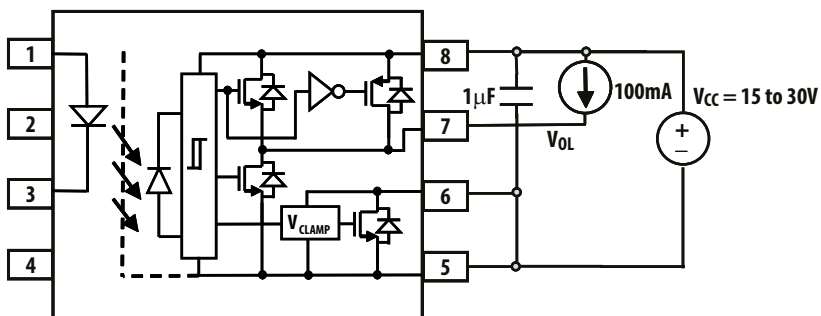


Figure 29: I_{CLAMP} Test Circuit

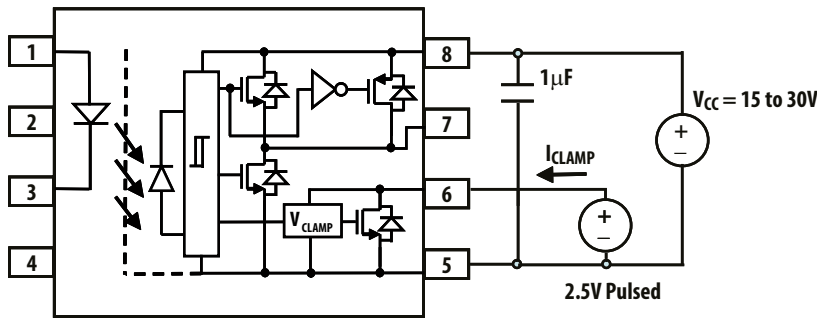


Figure 30: V_{tCLAMP} Test Circuit

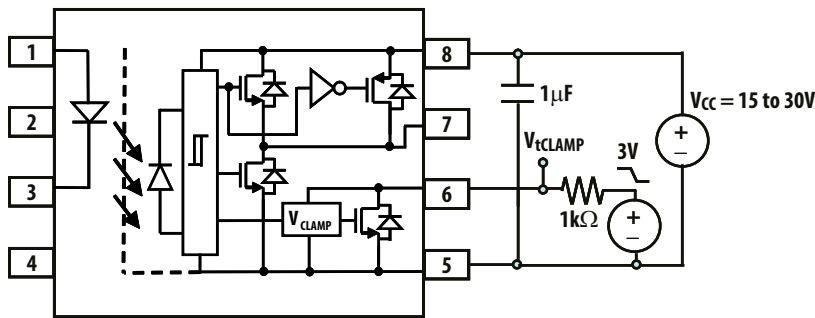


Figure 31: I_{FLH} Test Circuit

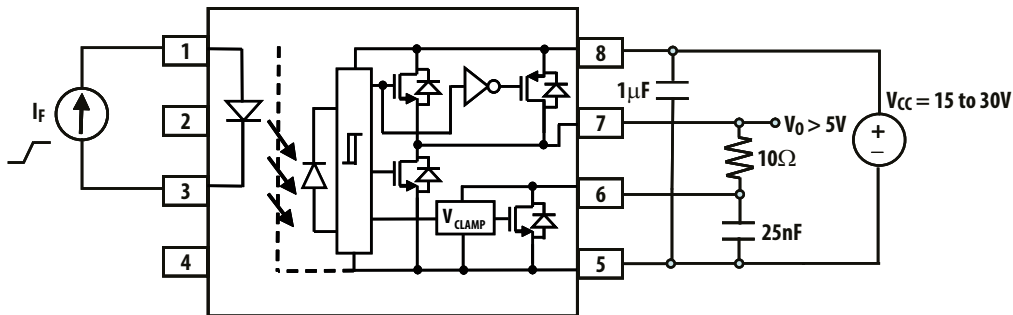


Figure 32: UVLO Test Circuit

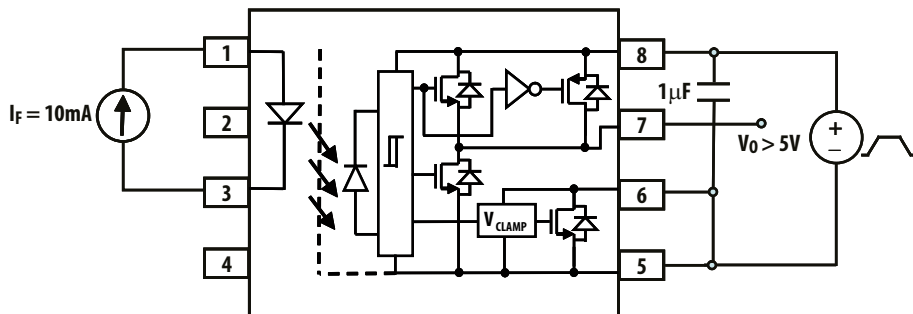


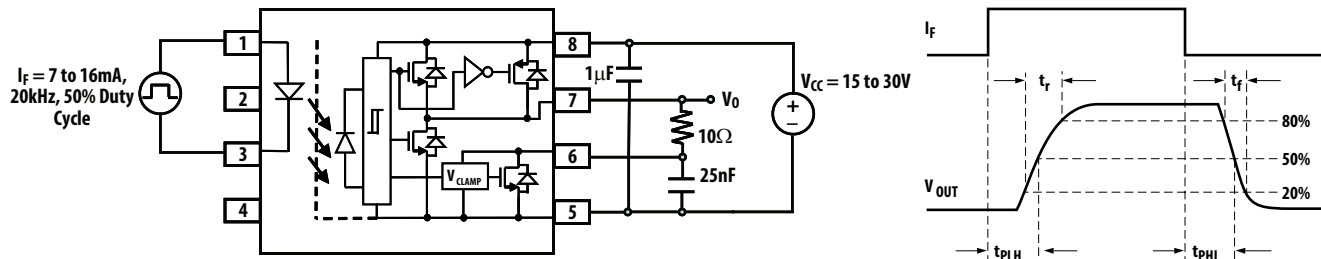
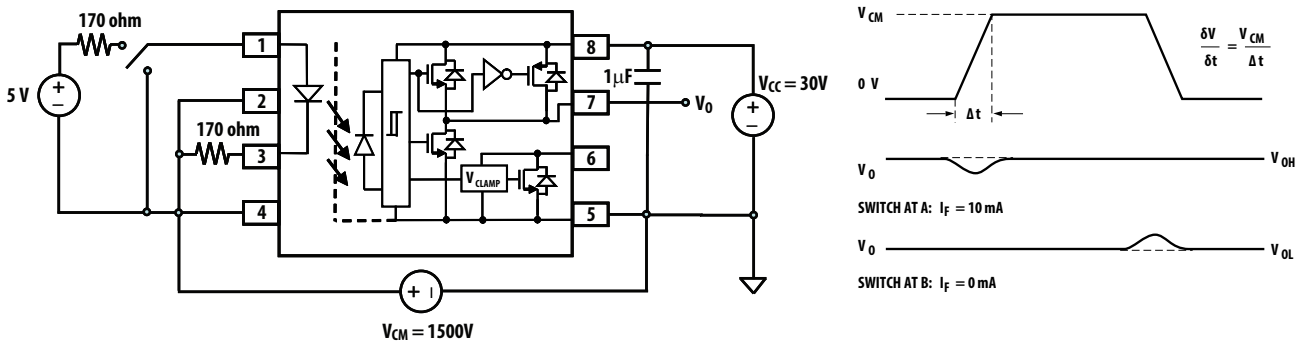
Figure 33: T_{PLH} , t_{PHL} , t_r , and t_f Test Circuit and Waveforms

Figure 34: CMR Test Circuit with Split Resistors Network and Waveforms



Application Information

Product Overview Description

The ACPL-H342/K342 is an optically isolated power output stage capable of driving IGBTs of up to 150A and 1200V. It has very high CMR rating which allows the microcontroller and the IGBT to operate at very large common mode noise found in industrial motor drives and other power switching applications. And to achieve better system reliability in such noisy environment, this power control device incorporates new features like active Miller clamp, rail-to-rail output voltage, anti-cross conduction and LED input current hysteresis.

The active Miller clamp function eliminates the need of negative gate drive in most application and allows the use of simple bootstrap supply for high side driver. Rail-to-rail output voltage ensures that the IGBT gate voltage is driven to the optimum intended level with no power loss across IGBT. Anti-cross conduction prevents current shoot through between the high and low side of half bridge IGBT configuration. This helps to simplify the controller design in terms of having to account for the delay needed at the LED

input. And lastly, the LED input current hysteresis prevents output oscillation if insufficient LED driving current is applied. This eliminates the need of additional Schmitt trigger circuit at the input LED.

This feature rich IGBT gate driver is designed to increase the performance and reliability of a motor drive without the cost, size, and complexity of external circuitry or control.

Recommended Application Circuit

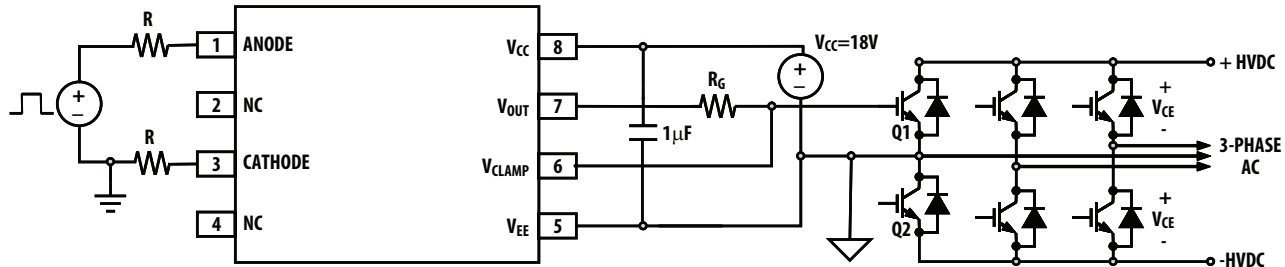
The recommended application circuit shown in [Figure 35](#) illustrates a typical gate drive implementation using the ACPL-H342. The following describes about driving IGBT. However, it is also applicable to MOSFET. Designers need to adjust the V_{CC} supply voltage, depending on the MOSFET or IGBT gate threshold requirements (recommended $V_{CC} = 18V$ for IGBT and $12V$ for MOSFET).

The supply bypass capacitors ($1 \mu F$) provide the large transient currents necessary during a switching transition. Because of the transient nature of the charging currents, a low current (2.5 mA) power supply is enough to power the device. The split resistors across the LED provide a high CMR response by providing a balanced resistance network across the LED.

The gate resistor R_G serves to limit gate charge current and controls the IGBT collector voltage rise and fall times.

In PC board design, care should be taken to avoid routing the IGBT collector or emitter traces close to the ACPL-H342 input as this can result in unwanted coupling of transient signals into ACPL-H342 and degrade performance.

Figure 35: Recommended Application Circuit with Split Resistors LED Drive and Active Miller Clamp



Active Miller Clamp

A Miller clamp allows the control of the Miller current during a high dV/dt situation. And it can also eliminate the use of a negative supply voltage by quickly discharging the large gate capacitance of IGBT to low level without affecting the IGBT turn-off characteristics. During turn-off, the gate voltage is monitored and the clamp output is activated when gate voltage goes below 2.3V (relative to V_{EE}). The clamp voltage is $V_{OL} + 2.5V$ typ. for a Miller current up to 2.5A. The clamp is disabled when the LED input is triggered again.

The AN5314 application note describes how the clamp reduces the parasitic turn-on effect due to the Miller capacitor and at the same time eliminates the need of a negative power supply.

The Miller pin should be connected to V_{EE} when not in use.

Rail-to-Rail Output

Figure 36 shows a typical gate driver's high current output stage with three bipolar transistors in Darlington configuration. During the output high transition, the output voltage rises rapidly to within three diode drops of V_{CC} . To ensure the V_{OUT} is at V_{CC} in order to achieve IGBT rated $V_{CE(ON)}$ voltage. The level of V_{CC} needs to be raised to beyond $V_{CC} + 3(V_{BE})$ to account for the diode drops. And to limit the output voltage to V_{CC} , a pull-down resistor, $R_{PULL-DOWN}$ between the output and V_{EE} is recommended to sink a static current while the output is high.

ACPL-H342 uses a power NMOS follower stage to deliver the initial large current and a smaller PMOS to pull it to V_{CC} to achieve rail-to-rail output voltage as shown in Figure 37. This ensures that the IGBT gate voltage is driven to the optimum intended level with no power loss across IGBT even when an unstable power supply is used.

Figure 36: Typical Gate Drive with Output Stage in Darlington Configuration

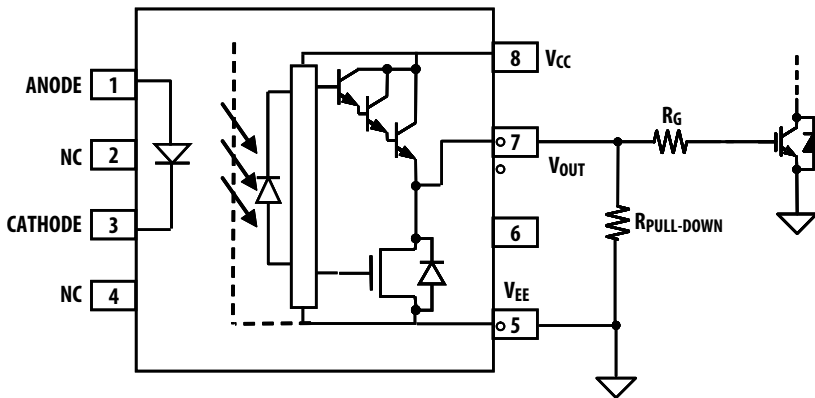
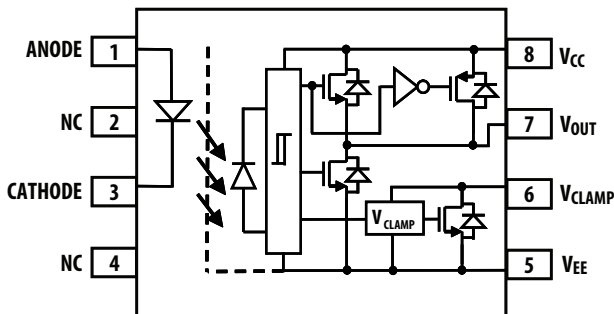


Figure 37: ACP-H342 with NMOS and PMOS Output Stage for Rail-to-Rail Output Voltage



Selecting the Gate Resistor (Rg)

Step 1: Calculate Rg minimum from the I_{OL} peak specification. The IGBT and Rg in Figure 35 can be analyzed as a simple RC circuit with a voltage supplied by ACPL-H342/K342.

$$R_g \geq \frac{V_{CC} - V_{EE} - V_{OL}}{I_{OLPEAK}}$$

$$= \frac{18V - 0V - 2.3V}{2.5A}$$

$$= 6.28\Omega \approx 7\Omega$$

The V_{OL} value of 2.3V in the previous equation is the V_{OL} at the peak current of 2.5A (see Figure 9).

Step 2: Check the ACPL-H342/K342 power dissipation and increase Rg if necessary. The ACPL-H342/K342 total power dissipation (P_T) is equal to the sum of the emitter power (P_E) and the output power (P_O).

$$P_T = P_E + P_O$$

$$P_E = I_F \times V_F \times \text{Duty Cycle}$$

$$P_O = P_{O(BIAS)} + P_{O(SWITCHING)}$$

$$= I_{CC} \times (V_{CC} - V_{EE}) + E_{SW} (R_g; Q_g) \times f$$

Using I_F (worst case) = 16 mA, $R_g = 7\Omega$, Max Duty Cycle = 80%, $Q_g = 500$ nC, $f = 25$ kHz and $T_A \text{ max} = 85^\circ\text{C}$:

$$P_E = 16 \text{ mA} \times 1.95V \times 0.8 = 25 \text{ mW}$$

$$P_O = 2.5 \text{ mA} \times 18V + 4 \mu\text{J} \times 25 \text{ kHz}$$

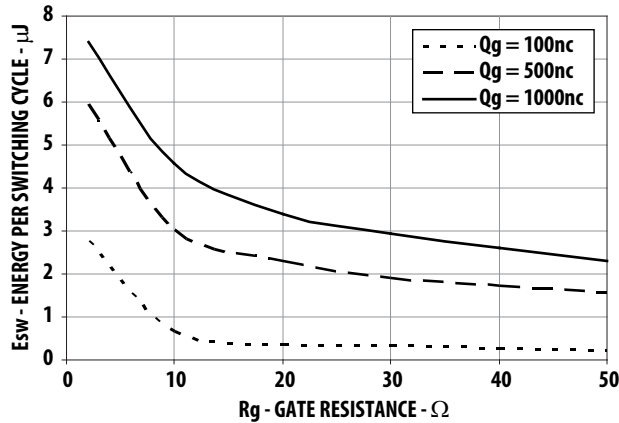
$$= 45 \text{ mW} + 100 \text{ mW}$$

$$= 145 \text{ mW} < 500 \text{ mW } (P_{O(MAX)} @ 85^\circ\text{C})$$

The value of 2.5 mA for I_{CC} in the previous equation is the maximum I_{CC} over the entire operating temperature range.

Since P_O is less than $P_{O(MAX)}$, $R_g = 7\Omega$ is alright for the power dissipation.

Figure 38: Energy Dissipated in the ACPL-H342/K342 for Each IGBT Switching Cycle



Anti-Cross Conduction to Prevent Current Shoot-Through and Determining Dead Time

The ACPL-H342 includes a Propagation Delay Difference ($PDD = t_{PHL} - t_{PLH}$) specification to help prevent both the high(Q1) and low(Q2) side power transistors from turning on at the same time. This *Anti-Cross* conduction feature prevents large currents from flowing through the power transistors by ensuring $t_{PHL_{MAX}}$ is faster than $t_{PLH_{MIN}}$. In other words, the Anti-Cross feature ensures one power transistor is turned off before the other is turned on.

A gate driver without Anti-Cross feature for example has a PDD_{MIN} of -350 ns and a PDD_{MAX} of 350 ns. A positive PDD_{MAX} of 350 ns means one transistor is turned on before the other is off since $t_{PHL_{MAX}}$ is longer than $t_{PLH_{MIN}}$. This is shown in Figure 40. To prevent this and the shoot-through current, the turn on of LED2 should be delayed (relative to the turn off of LED1) so that under worst-case conditions, Q1 has just turned off when Q2 turns on. The amount of delay to achieve this condition is equal to PDD_{MAX} as shown in Figure 41.

Figure 39: Prevent Current Shoot-Through in a Half-Bridge Topology

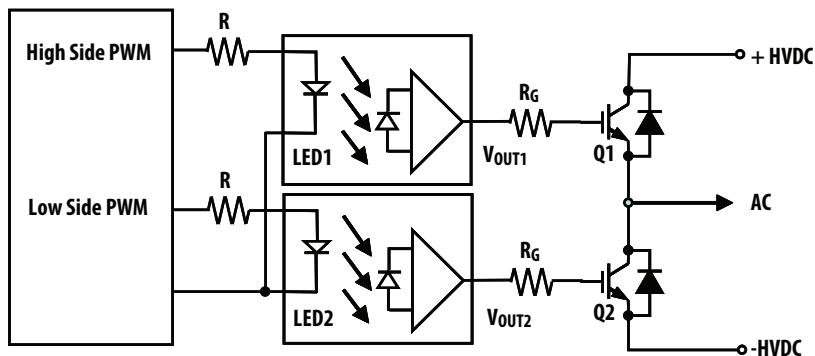


Figure 40: Current Shoot Through without Anti-Cross Feature

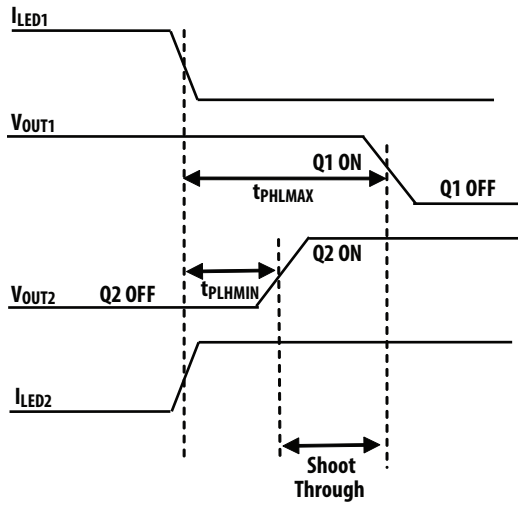
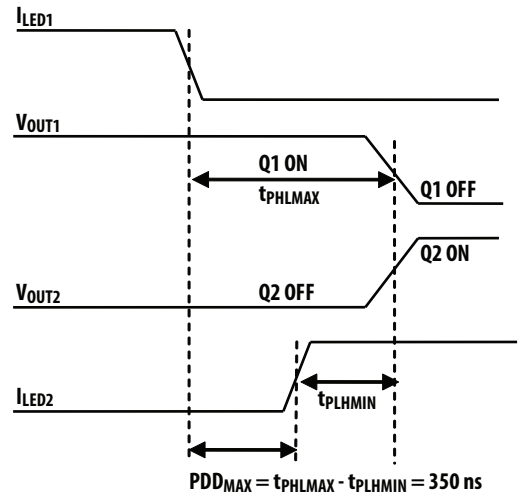


Figure 41: Adding Delay to Prevent Shoot Through



The ACPL-H342 with the Anti-Cross feature has a PDD_{MIN} of -10 ns and a PDD_{MAX} of -200 ns. Since the PDD is always a negative value, the t_{PHLMAX} is always faster than t_{PLHMIN} . Thus this simplified the design without having to add any amount of delay for the input LEDs as shown in Figure 42.

Symbol	Min.	Typ.	Max.	Unit
t_{PLH}	0.100	0.260	0.350	μ s
t_{PHL}	0.050	0.145	0.250	μ s
PDD ($t_{PHL} - t_{PLH}$)	-0.010	-0.100	-0.200	μ s

Figure 42: Anti-Cross to Prevent Shoot Through

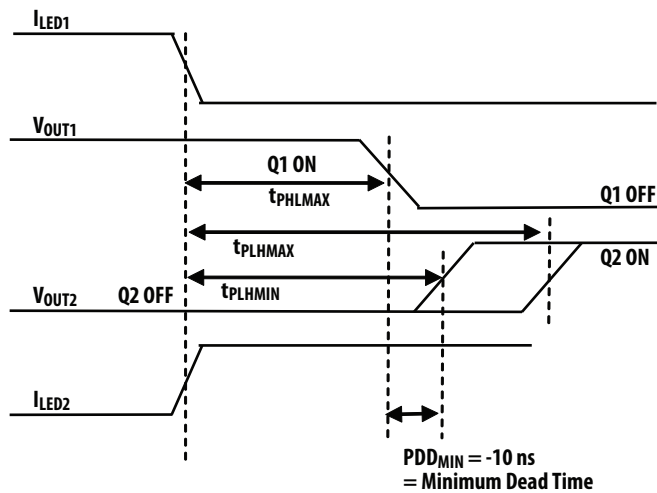
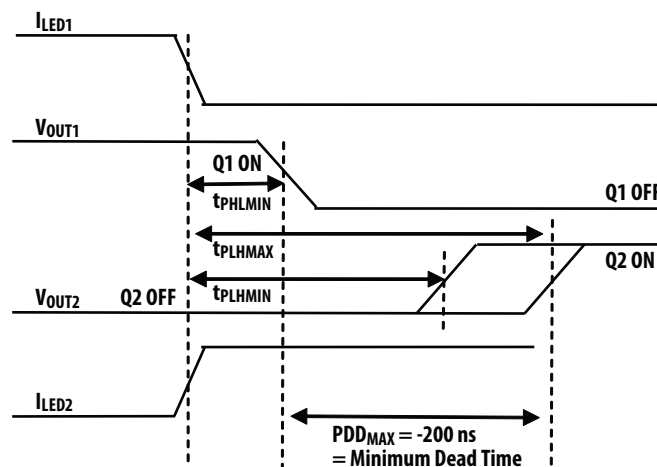
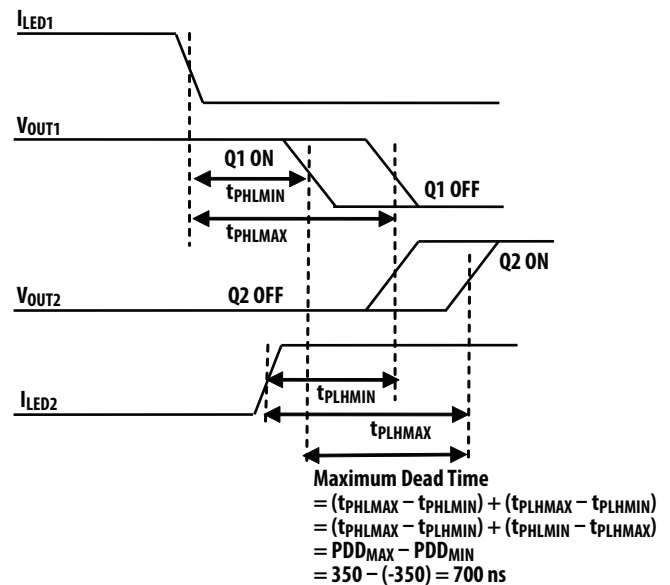


Figure 43: Determining Maximum Dead Time



Dead time is the time period during which both the high(Q1) and low(Q2) side transistor are off. During this time, no work is done and this reduces the efficiency of the inverter or motor drive. The minimum and maximum dead time is shown in Figure 42 and Figure 43 and is equivalent to the PDD_{MIN} and PDD_{MAX} . Due to the smaller PDD and skewed propagation delay configuration, ACPL-H342 shows a smaller maximum dead time as compared to its predecessor, HCPL-3120 as shown in Figure 44 and hence an improve in efficiency. Note that the propagation delays used to calculate PDD and dead time are taken at equal temperature and test conditions since the optocouplers under consideration are typically mounted in close proximity to each other and are switching identical IGBTs.

Figure 44: HCPL-3120 Maximum Dead Time



LED Input Current Hysteresis

The detector has optical receiver input stage with built-in Schmitt trigger to provide logic compatible waveforms, eliminating the need for additional wave shaping. The hysteresis (Figure 14) provides differential mode noise immunity and minimizes the potential for output signal chatter.

Under Voltage Lockout

The ACPL-H342 under voltage lockout (UVLO) feature is designed to prevent the application of insufficient gate voltage to the IGBT by forcing the ACPL-H342 output low during power-up. IGBTs typically require gate voltages of 15V to achieve their rated $V_{CE(ON)}$ voltage. At gate voltages below 13V typically, the $V_{CE(ON)}$ voltage increases dramatically, especially at higher currents. At very low-gate voltages (below 10V), the IGBT can operate in the linear region and quickly overheat. The UVLO function causes the output to be clamped whenever insufficient operating supply (V_{CC}) is applied. Once V_{CC} exceeds V_{UVLO+} (the positive-going UVLO threshold), the UVLO clamp is released to allow the device output to turn on in response to input signals.

Thermal Model for ACPL-H342/K342 Stretched SO8 Package Optocoupler

Definitions:

R_{11} : Junction to Ambient Thermal Resistance of LED due to heating of LED.
 R_{12} : Junction to Ambient Thermal Resistance of LED due to heating of Detector (Output IC).

R_{21} : Junction to Ambient Thermal Resistance of Detector (Output IC) due to heating of LED.

R_{22} : Junction to Ambient Thermal Resistance of Detector (Output IC) due to heating of Detector (Output IC).

P_1 : Power dissipation of LED (W).

P_2 : Power dissipation of Detector/Output IC (W).

T_1 : Junction temperature of LED ($^{\circ}\text{C}$).

T_2 : Junction temperature of Detector ($^{\circ}\text{C}$).

T_A : Ambient temperature.

Ambient Temperature: Junction to ambient thermal resistances were measured approximately 1.25 cm above optocoupler at $\sim 23^{\circ}\text{C}$ in still air.

Thermal Resistance	$^{\circ}\text{C}/\text{W}$
R_{11}	145
R_{12}, R_{21}	25, 38
R_{22}	46

This thermal model assumes that an 8-pin single-channel plastic package optocoupler is soldered into a 7.62 cm \times 7.62 cm printed circuit board (PCB) per JEDEC standards. The temperature at the LED and Detector junctions of the optocoupler can be calculated using the equations below.

$$T_1 = (R_{11} \times P_1 + R_{12} \times P_2) + T_A \quad (1)$$

$$T_2 = (R_{21} \times P_1 + R_{22} \times P_2) + T_A \quad (2)$$

Using the given thermal resistances and thermal model formula in this data sheet, we can calculate the junction temperature for both LED and the output detector. Both junction temperature should be within the absolute maximum rating.

For example, given $P_1 = 45 \text{ mW}$, $P_2 = 210 \text{ mW}$, $T_a = 85^{\circ}\text{C}$.

LED junction temperature:

$$\begin{aligned} T_1 &= (R_{11} \times P_1 + R_{12} \times P_2) + T_A \\ &= (145 \times 0.045 + 25 \times 0.210) + 85 \\ &= 97^{\circ}\text{C} \end{aligned}$$

Output IC junction temperature:

$$\begin{aligned} T_2 &= (R_{21} \times P_1 + R_{22} \times P_2) + T_A \\ &= (38 \times 0.045 + 46 \times 0.210) + 85 \\ &= 96^{\circ}\text{C} \end{aligned}$$

T_1 and T_2 should be limited to 125°C based on the board layout and part placement.

Related Application Notes

AN5336 – *Gate Drive Optocoupler Basic Design for IGBT/MOSFET*

AN1043 – *Common-Mode Noise: Sources and Solutions*

AN02-0310EN – *Plastics Optocouplers Product ESD and Moisture Sensitivity*